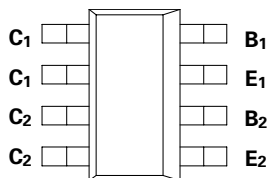


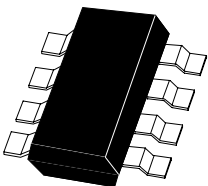
SM-8 DUAL PNP MEDIUM POWER
TRANSISTORS

ISSUE 1 - JULY 1999

ZDT795A



PARTMARKING DETAIL – T795A



SM-8
(8 LEAD SOT223)

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-140	V
Collector-Emitter Voltage	V_{CEO}	-140	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-1	A
Continuous Collector Current	I_C	-0.5	A
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	°C

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	VALUE	UNIT
Total Power Dissipation at $T_{amb} = 25^{\circ}C^*$ Any single die "on" Both die "on" equally	P_{tot}	2.25 2.75	W W
Derate above $25^{\circ}C^*$ Any single die "on" Both die "on" equally		18 22	mW/ °C mW/ °C
Thermal Resistance - Junction to Ambient* Any single die "on" Both die "on" equally		55.6 45.5	°C/ W °C/ W

* The power which can be dissipated assuming the device is mounted in a typical manner on a PCB with copper equal to 2 inches square.

ZDT795A

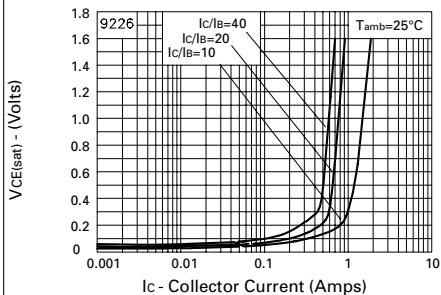
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-140			V	$I_C = -100\mu\text{A}$, $I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-140			V	$I_C = -10\text{mA}$, $I_B = 0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu\text{A}$, $I_C = 0$
Collector Cutoff Current	I_{CBO}			-0.1	μA	$V_{CB} = -100\text{V}$
Emitter Cutoff Current	I_{EBO}			-0.1	μA	$V_{EB} = -4\text{V}$, $I_E = 0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.3 -0.3 -0.25	V V V	$I_C = -100\text{mA}$, $I_B = -1\text{mA}^*$ $I_C = -200\text{mA}$, $I_B = -5\text{mA}^*$ $I_C = -500\text{mA}$, $I_B = -50\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-0.95	V	$I_C = -500\text{mA}$, $I_B = -50\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.75		V	$I_C = -500\text{mA}$, $V_{CE} = -2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	300 250 100		800		$I_C = -10\text{mA}$, $V_{CE} = -2\text{V}^*$ $I_C = -200\text{mA}$, $V_{CE} = -2\text{V}^*$ $I_C = -300\text{mA}$, $V_{CE} = -2\text{V}^*$
Transition Frequency	f_T	100			MHz	$I_C = -50\text{mA}$, $V_{CE} = -5\text{V}$ $f = 50\text{MHz}$
Output Capacitance	C_{obo}		15		pF	$V_{CB} = -10\text{V}$ $f = 1\text{MHz}$
Switching Times	t_{on}		100		ns	$I_C = -100\text{mA}$, $V_{CC} = -50\text{V}$ $I_{B1} = I_{B2} = -10\text{mA}$
	t_{off}		1900		ns	

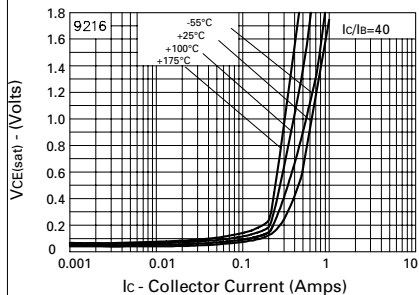
*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

ZDT795A

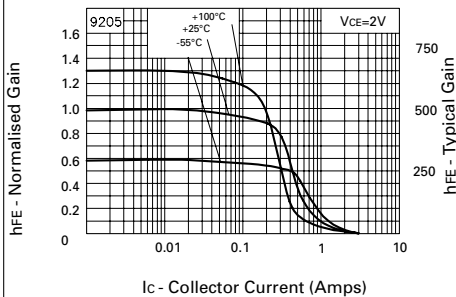
TYPICAL CHARACTERISTICS



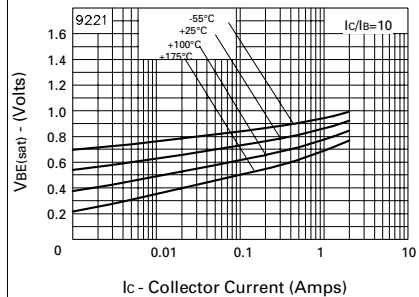
$V_{CE(sat)}$ v I_C



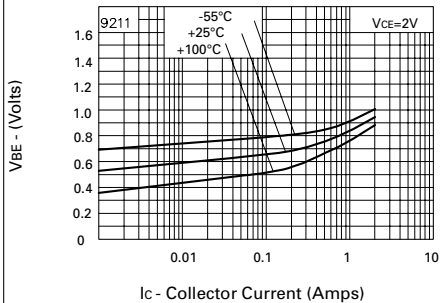
$V_{CE(sat)}$ v I_C



h_{FE} v I_C



$V_{BE(sat)}$ v I_C



$V_{BE(on)}$ v I_C